

# Abstracts

## The Relationship of Magnetotransconductance Mobility Profiles and RF Performance of GaAs FETs

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*S.K. Chan, K.M. Lau and P.M. White. "The Relationship of Magnetotransconductance Mobility Profiles and RF Performance of GaAs FETs." 1985 MTT-S International Microwave Symposium Digest 85.1 (1985 [MWSYM]): 204-206.*

The mobility profiles of FET channels were measured on fabricated low noise and power GaAs MESFETs, using the recently developed magnetotransconductance technique. The results are used to study the correlation between the RF performance and the material parameter.

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